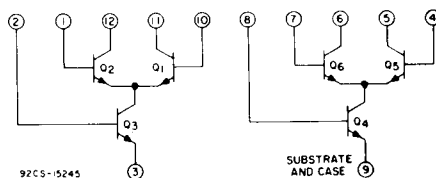


High-Reliability

Transistor Array

Dual Independent Differential Amplifier

The CA3026 (/) Series type is supplied in the 12-lead TO-5 style package.



Schematic Diagram

TABLE A. POST BURN-IN, FINAL ELECTRICAL AND GROUP A SAMPLING TESTS

CHARACTERISTIC	SYMBOL	TEST CONDITIONS	LIMITS FOR INDICATED TEMPERATURES (°C)						UNITS
			MINIMUM			MAXIMUM			
			-55	+25	+125	-55	+25	+125	
For Each Transistor:									
Collector Cutoff Current	I_{CBO}	$V_{CB} = 10 \text{ V}, I_E = 0$	—	—	—	0.1	0.1	20	μA
Collector To-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C = 10 \mu\text{A}, I_E = 0$	—	20	—	—	—	—	V
Emitter-To-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E = 10 \mu\text{A}, I_C = 0$	—	5	—	—	—	—	V
Collector-To-Substrate Breakdown Voltage	$V_{(BR)C10}$	$I_C = 10 \mu\text{A}, I_{C1} = 0$	—	20	—	—	—	—	V
Collector-To-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = 1 \text{ mA}, I_B = 0$	—	15	—	—	—	—	V
Input Bias Current For Transistors Q3 and Q4	I_I	$V_{CE} = 3 \text{ V}, I_E = 2 \text{ mA}$	—	—	—	100	50	40	μA
Input Bias Current For Transistors Q1, Q2, Q5, and Q6	I_I	$V_{CE} = 3 \text{ V}, I_E = 1 \text{ mA}$	—	—	—	50	25	20	μA
Base-To-Emitter Voltage For Transistors Q3 and Q4	V_{BE}	$V_{CE} = 3 \text{ V}, I_E = 1 \text{ mA}$	0.7	0.7	0.4	1.05	0.8	0.75	V
For Each Differential Amplifier									
Input Offset Current	I_{IO}	$V_{CE} = 3 \text{ V}, I_E = 2 \text{ mA}$	—	—	—	—	2	—	μA
Input Offset Voltage	V_{IO}	$V_{CE} = 3 \text{ V}, I_E = 2 \text{ mA}$	—	—	—	—	5	—	mV

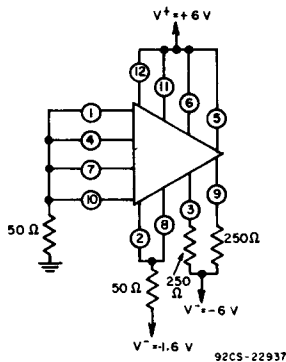
CA3026/...

TABLE B. DELTA LIMITS at $T_A = 25^\circ\text{C}$ (/1 only)

CHARACTERISTIC	SYMBOL	TEST CONDITIONS	LIMITS	UNITS
			MAX. Δ	
Input Bias Current For Each Transistor Q1, Q2, Q5, and Q6	I_I	$V_{CE} = 3\text{V}, I_E = 2\text{mA}$	± 6.0	μA
Base-to-Emitter Voltage For Each Transistor Q3 and Q4	V_{BE}	$V_{CE} = 3\text{V}, I_E = 1\text{mA}$	± 0.1	V
Input Offset Voltage For Each Differential Amplifier	V_{IO}	$V_{CE} = 3\text{V}, I_E = 2\text{mA}$	± 2	mV

TABLE C. GROUPS C AND D END-POINT TESTS at $T_A = 25^\circ\text{C}$

CHARACTERISTIC	SYMBOL	TEST CONDITIONS	LIMITS		UNITS
			MIN.	MAX.	
For Each Transistor: Collector Cutoff Current	I_{CBO}	$V_{CB} = 10\text{V}, I_E = 0$	—	0.2	μA
Input Bias Current For Transistors Q1, Q2, Q5, & Q6	I_I	$V_{CE} = 3\text{V}, I_E = 2\text{mA}$	—	28	μA
Base-to-Emitter Voltage For Transistors Q3 and Q4	V_{BE}	$V_{CE} = 3\text{V}, I_E = 1\text{mA}$	0.65	0.85	V
For Each Differential Amplifier: Input Offset Voltage	V_{IO}	$V_{CE} = 3\text{V}, I_E = 2\text{mA}$	—	6	mV



Burn-in and operating life test circuit.